

Automotive N-Channel 55 V (D-S) 175 °C MOSFET

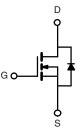
PRODUCT SUMMARY					
V _{DS} (V)	55				
$R_{DS(on)}\left(\Omega\right)$ at V_{GS} = 10 V	0.020				
$R_{DS(on)}\left(\Omega\right)$ at V_{GS} = 4.5 V	0.026				
I _D (A)	30				
Configuration	Single				
Package	TO-252				



FEATURES

- TrenchFET[®] power MOSFET
- 100 % R_g and UIS tested
- AEC-Q101 qualified d
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>





N-Channel MOSFET

ABSOLUTE MAXIMUM RATIN	GS (T _C = 25 °C, unless	otherwise noted	l)	
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-Source Voltage		V _{DS}	55	M
Gate-Source Voltage		V _{GS}	± 20	V
Continuous Drain Current	T _C = 25 °C ª	1	30	
Continuous Drain Current	T _C = 125 °C	· I _D	19	
Continuous Source Current (Diode Conduc	ction) ^a	۱ _S	30	А
Pulsed Drain Current ^b		I _{DM}	120	
Single Pulse Avalanche Current	L = 0.1 mH	I _{AS}	20	
Single Pulse Avalanche Energy		E _{AS}	20	mJ
Maximum Power Dissipation ^b	T _C = 25 °C	Р	50	W
Maximum Fower Dissipation 5	T _C = 125 °C	P _D	16	vv
Operating Junction and Storage Temperature Range		T _J , T _{stg}	-55 to +175	°C

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	LIMIT	UNIT	
Junction-to-Ambient	PCB Mount ^c	ount ^c R _{thJA} 60		°C/W	
Junction-to-Case (Drain)		R _{thJC}	3	0/₩	

Notes

- b. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.
- c. When mounted on 1" square PCB (FR4 material).
- d. Parametric verification ongoing.

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a. Package limited.

SQD30N05-20L



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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT	
Static	-							
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V}, \text{ I}_{D} = 250 \mu\text{A}$		55	-	-	V	
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} =	= V _{GS} , I _D = 250 μΑ	1.5	2	2.5	V	
Gate-Source Leakage	I _{GSS}	V _{DS} =	$V_{DS} = 0 V, V_{GS} = \pm 20 V$		-	± 100	nA	
		$V_{GS} = 0 V$	V _{DS} = 55 V	-	-	1		
Zero Gate Voltage Drain Current	I _{DSS}	$V_{GS} = 0 V$	V _{DS} = 55 V, T _J = 125 °C	-	-	50	μA	
		$V_{GS} = 0 V$	V _{DS} = 55 V, T _J = 175 °C	-	-	250		
On-State Drain Current ^a	I _{D(on)}	$V_{GS} = 5 V$	$V_{DS} \ge 5 V$	30	-	-	Α	
		V _{GS} = 10 V	I _D = 20 A	-	0.016	0.020	Ω	
		V _{GS} = 10 V	I _D = 20 A, T _J = 125 °C	-	-	0.035		
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 10 V	I _D = 20 A, T _J = 175 °C	-	-	0.043		
		$V_{GS} = 4.5 V$	I _D = 15 A	-	0.021	0.026		
Forward Transconductance b	9 _{fs}	V _{DS}	V _{DS} = 15 V, I _D = 20 A		34	-	S	
Dynamic ^b					•			
Input Capacitance	C _{iss}		V _{DS} = 25 V, f = 1 MHz	-	938	1175	pF	
Output Capacitance	C _{oss}	$V_{GS} = 0 V$		-	203	255		
Reverse Transfer Capacitance	C _{rss}			-	86	110		
Total Gate Charge ^c	Qg			-	12	18	nC	
Gate-Source Charge ^c	Q _{gs}	$V_{GS} = 5 V$	$V_{DS} = 25 \text{ V}, \text{ I}_{D} = 35 \text{ A}$	-	4.1	-		
Gate-Drain Charge ^c	Q _{gd}			-	4.8	-		
Gate Resistance	R _g		f = 1 MHz		2.1	4.5	Ω	
Turn-On Delay Time ^c	t _{d(on)}				7	11	- ns	
Rise Time ^c	t _r	$\label{eq:VDD} \begin{array}{l} V_{\text{DD}} = 25 \text{ V}, \ R_{\text{L}} = 0.71 \ \Omega \\ I_{\text{D}} \cong 35 \text{ A}, \ V_{\text{GEN}} = 10 \text{ V}, \ R_{\text{g}} = 1 \ \Omega \end{array}$		-	10	15		
Turn-Off Delay Time ^c	t _{d(off)}			-	18	27		
Fall Time ^c	t _f			-	5	8		
Source-Drain Diode Ratings and Chara	acteristics ^b							
Pulsed Current ^a	I _{SM}			-	-	120	Α	
Forward Voltage	V _{SD}	I _F = 80 A, V _{GS} = 0 V		1	1.2	1.5	V	

Notes

a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.

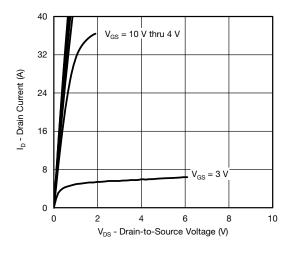
b. Guaranteed by design, not subject to production testing.

c. Independent of operating temperature.

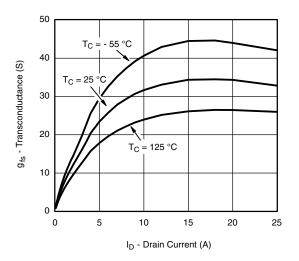
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



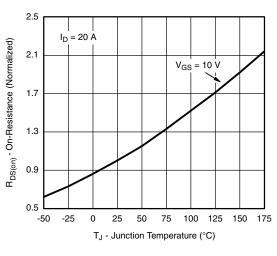
TYPICAL CHARACTERISTICS ($T_A = 25 \text{ °C}$, unless otherwise noted)



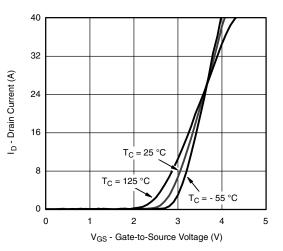
Output Characteristics



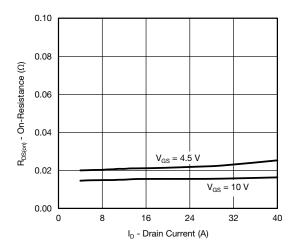
Transconductance

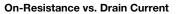


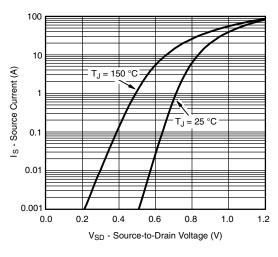
On-Resistance vs. Junction Temperature



Transfer Characteristics







Source Drain Diode Forward Voltage

S15-1873-Rev. D, 10-Aug-15

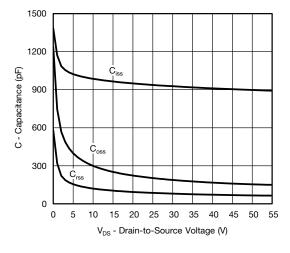
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Document Number: 67054

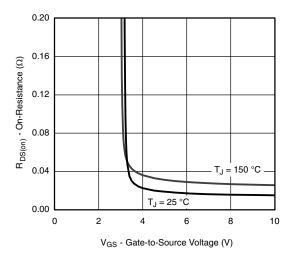
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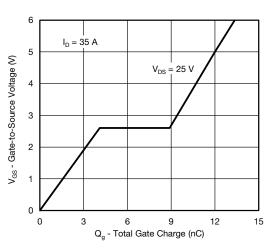
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



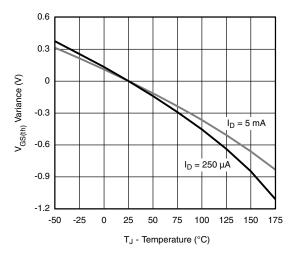




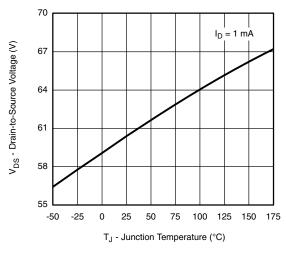
On-Resistance vs. Gate-to-Source Voltage











Drain Source Breakdown vs. Junction Temperature 4

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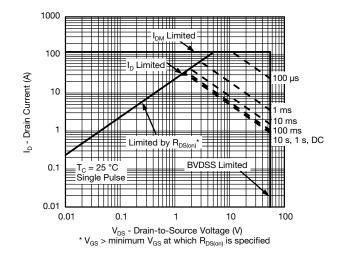
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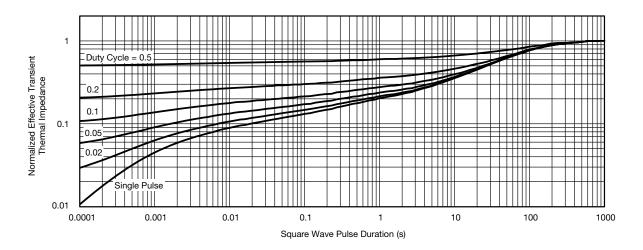
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THERMAL RATINGS ($T_A = 25 \text{ °C}$, unless otherwise noted)



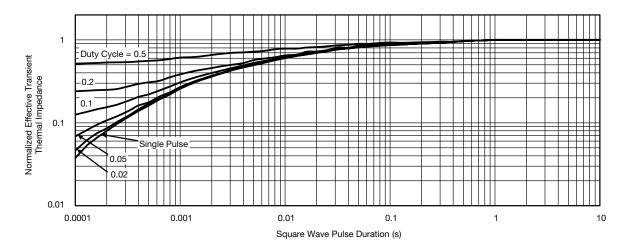
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient



THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

Note

• The characteristics shown in the two graphs

- Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)

- Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

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REVISION	HISTORY ^a	
REVISION	DATE	DESCRIPTION OF CHANGE
D	04-Aug-15	Revised R _g minimum limit

Note

a. As of April 2014





Е b3 Ľ Δ ŝ b2 e1 Б E1

C2 т gage plane height (0.5 mm)

-C

- A1

TO-252AA Case Outline

	MILLIN	IETERS	INCHES		
DIM.	MIN.	MAX.	MIN.	MAX.	
А	2.18	2.38	0.086	0.094	
A1	-	0.127	-	0.005	
b	0.64	0.88	0.025	0.035	
b2	0.76	1.14	0.030	0.045	
b3	4.95	5.46	0.195	0.215	
С	0.46	0.61	0.018	0.024	
C2	0.46	0.89	0.018	0.035	
D	5.97	6.22	0.235	0.245	
D1	4.10	-	0.161	-	
Е	6.35	6.73	0.250	0.265	
E1	4.32	-	0.170	-	
Н	9.40	10.41	0.370	0.410	
е	2.28 BSC 0.090 BSC			BSC	
e1	4.56	4.56 BSC		BSC	
L	1.40	1.78	0.055	0.070	
L3	0.89	1.27	0.035	0.050	
L4	-	1.02	-	0.040	
L5	1.01	1.52	0.040	0.060	
ECN: T13-0592-Rev. A, 02-Sep-13 DWG: 6019					

Note

• Dimension L3 is for reference only.





RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)



Recommended Minimum Pads Dimensions in Inches/(mm)

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